

MOC211-M MOC212-M MOC213-M

DESCRIPTION

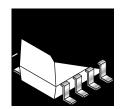
These devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector, in a surface mountable, small outline, plastic package. They are ideally suited for high density applications, and eliminate the need for through-the-board mounting.

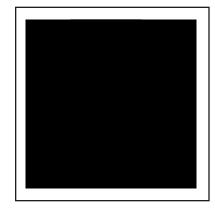
FEATURES

- UL Recognized (File #E90700, volume 2)
- VDE Recognized (File #136616) (add option 'V' for VDE approval, e.g., MOC211V-M)
- Convenient Plastic SOIC-8 Surface Mountable Package Style
- Standard SOIC-8 Footprint, with 0.050" Lead Spacing
- Compatible with Dual Wave, Vapor Phase and IR Reflow Soldering
- High Input-Output Isolation of 2500 V_{AC(rms)} Guaranteed
- Minimum BV_{CFO} of 30V guaranteed

APPLICATIONS

- General Purpose Switching Circuits
- Interfacing and coupling systems of different potentials and impedances
- Regulation Feedback Circuits
- Monitor and Detection Circuits







Detico	0	Value	11	
Rating	Symbol	Value	Unit	
EMITTER				
Forward Current – Continuous	I _F	60	mA	
Forward Current – Peak (PW = 100 μs, 120 pps)	I _F (pk)	1.0	А	
Reverse Voltage	V _R	6.0	V	
LED Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	90 0.8	mW mW/°C	
DETECTOR				
Collector-Emitter Voltage	V _{CEO}	30	V	
Emitter-Collector Voltage	V _{ECO}	7.0	V	
Collector-Base Voltage	V _{CBO}	70	V	
Collector Current-Continuous	I _C	150	mA	
Detector Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	150 mW 1.76 mW/°C		
TOTAL DEVICE				
Input-Output Isolation Voltage (1,2,3) (f = 60 Hz, t = 1 min.)	V _{ISO}	2500	Vac(rms)	
Total Device Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	250 2.94	mW mW/°C	
Ambient Operating Temperature Range	T _A	-40 to +100	°C	
Storage Temperature Range	T _{stg}	-40 to +150	°C	



Parameter Test Conditions		Symbol	Min	Тур**	Max	Unit
EMITTER						
Input Forward Voltage	$(I_F = 10 \text{ mA})$	V _F	_	1.15	1.5	V
Reverse Leakage Current	$(V_{R} = 6.0 \text{ V})$	I _R		0.001	100	μΑ
Input Capacitance		C _{IN}		18	_	pF
DETECTOR						
Collector-Emitter Dark Current	$(V_{CE} = 10 \text{ V}, T_A = 25^{\circ}\text{C})$ $(V_{CE} = 10 \text{ V}, T_A = 100^{\circ}\text{C})$	I _{CEO1}	_	1.0 1.0	50 —	nA μA
Collector-Emitter Breakdown Voltage	$(I_C = 100 \mu A)$	BV _{CEO}	30	90	_	V
Emitter-Collector Breakdown Voltage	(I _E = 100 μA)	BV _{ECO}	7.0	7.8	_	V
Collector-Emitter Capacitance	$(f = 1.0 \text{ MHz}, V_{CE} = 0)$	C _{CE}	_	7.0	_	pF
COUPLED Collector-Output Current ⁽⁴⁾	MOC211-M MOC212-M $(I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V})$ MOC213-M	CTR	20 50 100	65 90 140	_ _ _	%
Isolation Surge Voltage ^(1,2,3)	(60 Hz AC Peak, 1 min.)	V _{ISO}	2500	_	_	Vac(rms
Isolation Resistance ⁽²⁾	(V = 500 V)	R _{ISO}	10 ¹¹	_	_	Ω
Collector-Emitter Saturation Voltage	$(I_C = 2.0 \text{ mA}, I_F = 10 \text{ mA})$	V _{CE (sat)}	_	0.15	0.4	V
Isolation Capacitance ⁽²⁾	(V = 0 V, f = 1 MHz)	C _{ISO}	_	0.2	_	pF
Turn-On Time	$(I_C = 2.0 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100 \Omega)$ (Fig. 6)	t _{on}	_	7.5	_	μs
Turn-Off Time	$(I_C = 2.0 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100 \Omega)$ (Fig. 6)	t _{off}		5.7		μs
Rise Time	$(I_C = 2.0 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100 \Omega)$ (Fig. 6)	t _r		3.2	_	μs
Fall Time	$(I_C = 2.0 \text{ mA}, V_{CC} = 10 \text{ V}, R_L = 100 \Omega)$ (Fig. 6)	t _f	_	4.7	_	μs

^{**} Typical values at $T_A = 25$ °C

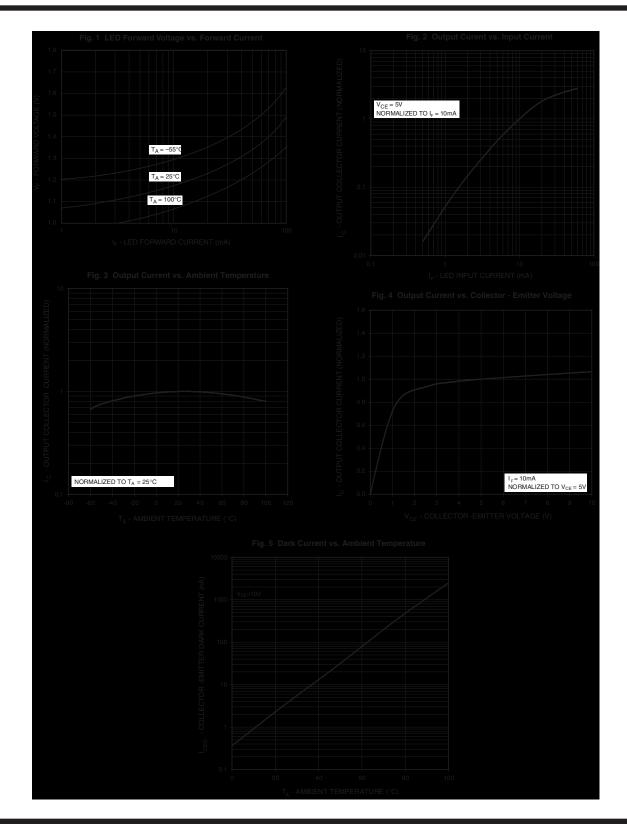
^{1.} Isolation Surge Voltage, V_{ISO} , is an internal device dielectric breakdown rating.

^{2.} For this test, Pins 1 and 2 are common and Pins 5, 6 and 7 are common.

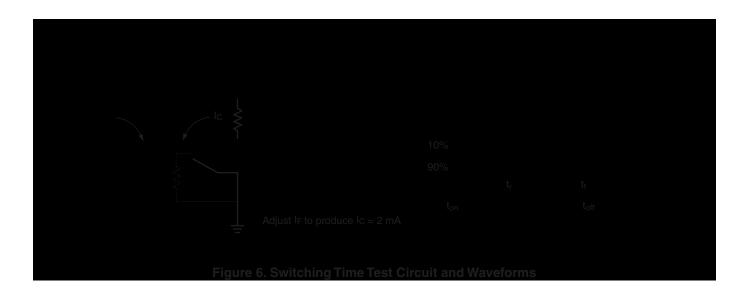
^{3.} V_{ISO} rating of 2500 $V_{AC(rms)}$ for t = 1 min. is equivalent to a rating of 3,000 $V_{AC(rms)}$ for t = 1 sec.

^{4.} Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.

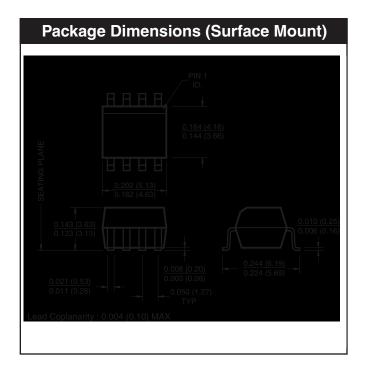


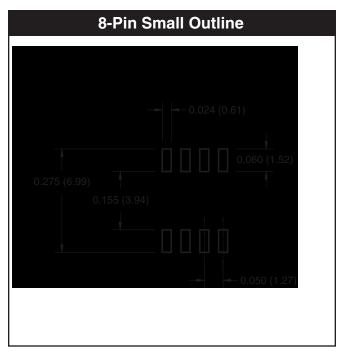












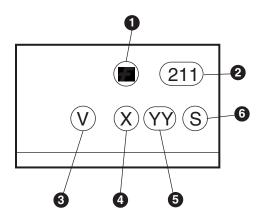


MOC211-M MOC212-M MOC213-M

ORDERING INFORMATION

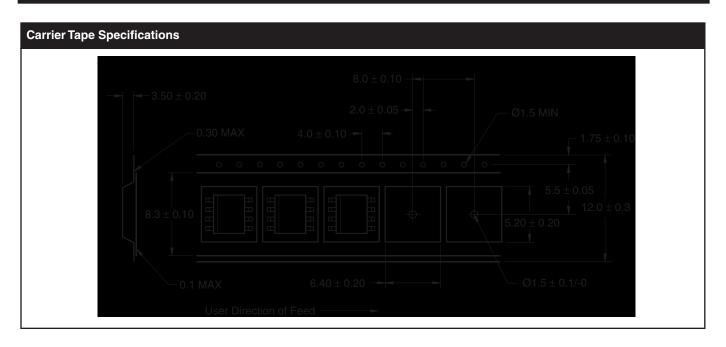
Option	Order Entry Identifier	Description
V	V	VDE 0884
R1	R1	Tape and reel (500 units per reel)
R1V	R1V	VDE 0884, Tape and reel (500 units per reel)
R2	R2	Tape and reel (2500 units per reel)
R2V	R2V	VDE 0884, Tape and reel (2500 units per reel)

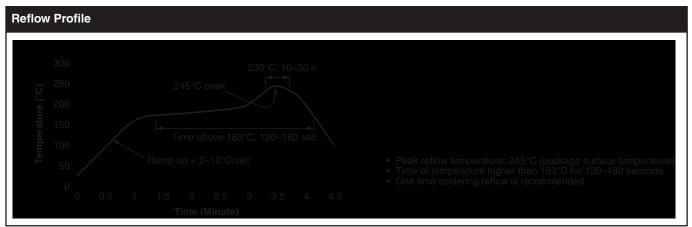
MARKING INFORMATION



Definitions				
1	Fairchild logo			
2	Device number			
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)			
4	One digit year code, e.g., '3'			
5	Two digit work week ranging from '01' to '53'			
6	Assembly package code			









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